CLAIMS:

1. A lithographic system comprising:

a lithographic apparatus with an anamorphic projection system; and

a radiation source configured to generate an EUV radiation emitting plasma at a plasma formation location, the EUV radiation emitting plasma having an elongate form in a plane substantially perpendicular to an optical axis of the radiation source, wherein the radiation source includes a pre-pulse laser which is configured to provide a laser pulse which causes a fuel droplet to expand by more in a first direction than in a second direction, the first and second directions being perpendicular to the direction of incidence of the laser pulse.

2. The lithographic system of claim 1, wherein the EUV radiation emitting plasma is generally elliptical in a plane perpendicular to the optical axis of the radiation source.

3. The lithographic system of claim 1 or claim 2, wherein the EUV radiation emitting plasma is elongate in a direction which corresponds with a major axis of a pupil of the anamorphic projection system.

4. The lithographic system of any preceding claim, wherein the laser pulse provided by the pre-pulse laser has a generally elliptical cross-section.

5. The lithographic system of any preceding claim, wherein the laser pulse provided by the pre-pulse laser is linearly polarized in the first direction.

6. The lithographic system of any preceding claim, wherein the radiation source includes a pre-pulse laser which is configured to cause a fuel droplet to expand to form a target which is tilted relative to an optical axis of the radiation source.

7. The lithographic system of claim 6, wherein the tilt of the target relative to the optical axis of the radiation source is between 30 degrees and 60 degrees.

8. The lithographic system of claim 6 or claim 7, wherein the target is generally disk-shaped.

9. The lithographic system of any preceding claim, wherein the radiation source comprises two or more lasers configured to provide laser beam waists which partially overlap at the plasma formation location.

10. The lithographic system of claim 9, wherein the two or more lasers are configured to provide laser beam pulses sequentially, such that a first portion of the EUV radiation emitting plasma is generated before a second portion of the EUV radiation emitting plasma is generated.

11. The lithographic system of claim 10, wherein the first and second portions of the EUV radiation emitting plasma are generated from the same fuel target.

12. A radiation source comprising a radiation source configured to generate an EUV radiation emitting plasma at a plasma formation location, the EUV radiation emitting plasma having an elongate form in a plane substantially perpendicular to an optical axis of the radiation source, wherein the radiation source includes a pre-pulse laser which is configured to provide a laser pulse which causes a fuel droplet to expand by more in a first direction than in a second direction, the first and second directions being perpendicular to the direction of incidence of the laser pulse.

13. The radiation source of claim 12, wherein the EUV radiation emitting plasma is generally elliptical in a plane perpendicular to the optical axis of the radiation source.

14. The radiation source of claim 12 or claim 13, wherein the radiation source includes a pre-pulse laser which is configured to cause a fuel droplet to expand to form a target which is tilted relative to an optical axis of the radiation source.

15. A lithographic system comprising:

a lithographic apparatus with an anamorphic projection system;

a first radiation source configured to generate an EUV radiation emitting plasma at a first plasma formation location and direct EUV radiation to a first intermediate focus; and,

a second radiation source configured to generate an EUV radiation emitting plasma at a second plasma formation location and direct EUV radiation to a second intermediate focus, the second intermediate focus being spatially displaced from the first intermediate focus; and

an illumination system configured to receive EUV radiation from the first and second intermediate focuses.

16. A lithographic method comprising

using a radiation source to generate an EUV radiation emitting plasma at a plasma formation location, the EUV radiation emitting plasma having an elongate form in a plane substantially perpendicular to an optical axis of the radiation source;

using an illumination system to condition the resulting EUV radiation;

patterning the EUV radiation in its cross-section to form a patterned radiation beam; and

projecting the patterned EUV radiation beam onto a substrate using an anamorphic projection system,

wherein the EUV radiation emitting plasma is elongate in a direction which corresponds with a major axis of a pupil of the anamorphic projection system.

17. The lithographic method of claim 16, wherein the EUV radiation emitting plasma is generally elliptical in a plane perpendicular to the optical axis of the radiation source.